

HIGH SPEED SWITCHING APPLICATION.

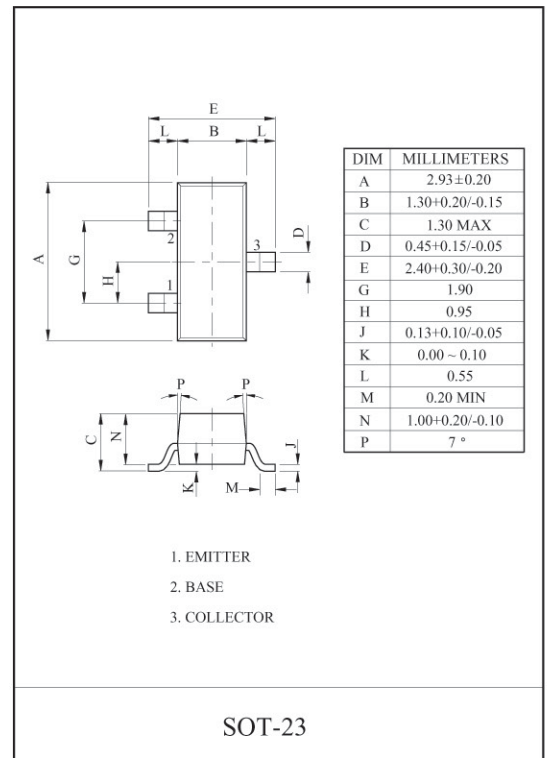
FEATURES

- Excellent High Frequency Characteristics.
- Excellent Switching Characteristics.

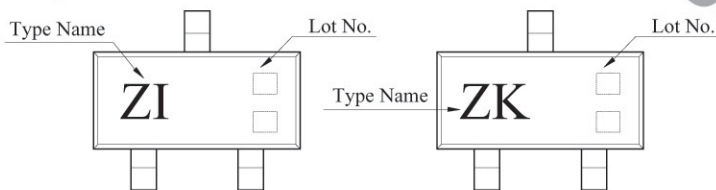
MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	4.5	V
Collector Current	I_C	500	mA
Collector Power Dissipation (Ta=25°C)	* P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

* Package Mounted On 99.5% Alumina 10x8x0.6mm.



Marking



MARK SPEC

TYPE	MARK
KTN2369S	Z I
KTN2369AS	Z K

KTN2369S/AS

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=20V, I_E=0$	-	-	0.4	μA
			$V_{CB}=20V, I_E=0, T_a=125^\circ C$	-	-	30	
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	40	-	-	V
Collector-Emitter Breakdown Voltage *		$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	15	-	-	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	4.5	-	-	
DC Current Gain *	KTN2369S/AS	h_{FE}	$I_C=10mA, V_{CE}=1.0V$	40	-	120	
	KTN2369S		$I_C=10mA, V_{CE}=1.0V, T_a=-55^\circ C$	20	-	-	
	KTN2369AS		$I_C=10mA, V_{CE}=0.35V, T_a=-55^\circ C$	20	-	-	
	KTN2369S		$I_C=100mA, V_{CE}=2.0V$	20	-	-	
	KTN2369AS		$I_C=100mA, V_{CE}=1.0V$	20	-	-	
Collector-Emitter Saturation Voltage *		$V_{CE(sat)}$	$I_C=10mA, I_B=1.0mA$	-	-	0.25	V
Base-Emitter Saturation Voltage *		$V_{BE(sat)}$	$I_C=10mA, I_B=1.0mA$	0.70	-	0.85	V
Collector Output Capacitance		C_{ob}	$V_{CB}=5.0V, I_E=0, f=1.0MHz$	-	-	4.0	pF
Storage Time		t_{stg}	$I_C=100mA, I_{B1}=-I_{B2}=10mA, V_{CC}=10V$	-	-	13	nS
Turn-on Time		t_{on}	$I_C=10mA, I_{B1}=3.0mA, V_{CC}=3.0V, I_{B2}=-1.5mA$	-	-	12	
Turn-off Time		t_{off}	$I_C=10mA, I_{B1}=3.0mA, I_{B2}=-1.5mA, V_{CC}=3.0V$	-	-	15	

* Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.